AMENDMENTS TO THE CLAIMS:

The listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

- 1. (Original) An electroluminescent device, comprising a semi-reflecting structure, a reflecting structure, and a plurality of intermediate layers for light generation, wherein said semi-reflecting structure thickness is chosen to cause destructive optical interference of ambient light reflected thereby, and said intermediate layers have thicknesses chosen to create a microcavity for causing constructive optical interference of light generated therein and approximately 360° phase change of transmitted ambient light passing therethrough from said semi-reflecting structure and reflecting off said reflecting structure, such that said transmitted ambient light is subjected to further destructive optical interference within said semi-reflecting structure.
- 2. (Original) The electroluminescent device of claim 1, wherein said intermediate layers include a hole-carrier layer and electron-carrier layer with a light generating region at the interface therebetween.
- 3. (Original) The electroluminescent device of claim 2, wherein said holecarrier layer comprises TPD and said electron-carrier layer comprises A1Q3.
- 4. (Original) The electroluminescent device of claim 3, wherein said intermediate layers include a buffer layer of CuPC adjacent said TPD layer.
- 5. (Original)The electroluminescent device of claim 4, wherein said intermediate layers include a conductive layer of ITO adjacent said CuPC layers.
- 6. (Original) The electroluminescent device of claim 5, wherein said thicknesses of the intermediate layers are as follows: A1Q3 = 200 to 800 Å, TPD = 200 to 500 Å, CuPC = 0 to 500 Å, ITO = 0 to 2500 Å.
- 7. (Original) The electroluminescent device of claim 1, wherein said semireflecting structure comprises at least one layer of A1, SiO2 and Cr.

- 8. (Original) The electroluminescent device of claim 1, wherein said reflecting structure comprises a layer of A1.
- 9. (Currently amended) The electroluminescent device of any of claims 1 to 8claim 1, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.
- 10. (Currently amended) The electroluminescent device of any of elaims 1 to 8claim 1, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.
- 11. (Original) The electroluminescent device of claim 10, wherein said substrate is one of either clear plastic or glass.
- 12. (Original) The electroluminescent device of claim 1, wherein said intermediate layers include one of either light emitting polymers or inorganic light emitting materials.
- 13. (Original) The electroluminescent device of claim 7, wherein said semireflecting structure comprises A1SiO (ratio 3:2, 5.5nm), SiO2 (60nm), and aluminum (10 nm).
- 14. (Original) The electroluminescent device of claim 6, wherein said thicknesses of the intermediate layers are as follows: A1Q3 = 600 Å, TPD = 450 Å, CuPC = 250 Å, ITO = 1200 Å.
- 15. (Previously presented) The electroluminescent device of claim 1, wherein said intermediate layers are selected such that the 360° phase change extends over the visible light range.
- 16. (Previously presented) The electroluminescent device of claim 1, wherein the layers are selected to have a refractive index that increases with wavelength.
- 17. (New) The electroluminescent device of any of claim 7, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.
 - 18. (New) The electroluminescent device of any of claim 7, wherein said

semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.

- 19. (New) The electroluminescent device of any of claim 8, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.
- 20. (New) The electroluminescent device of any of claim 8, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.